

India's First Silicon Carbide Facility

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Why in the News?

India's first silicon carbide manufacturing plant is set to be established in Odisha with an investment of Rs 620 crore.

• The facility, developed by **RIR Power Electronics Limited**, a key player in semiconductor power electronics, *will be located at EMC Park in Infovalley*, Bhubaneswar.

Silicon Carbide (SiC)

- It is a compound made of silicon and carbon.
- It has excellent heat conductivity, which makes it ideal for high-temperature applications.
- It is chemically inert and resistant to corrosion by acids, alkalis and salts.
- It has a very high melting point, around 2,730°C (4,950°F).

Acheson process: It is produced by this process where silica (SiO?) and carbon (usually in the form of petroleum coke) are heated to high temperatures in an electric furnace.

• This process forms SiC crystals and releases carbon dioxide as a by-product.

Uses

- **High-temperature semiconductor devices like** *diodes, MOSFETs* (metal-oxide-semiconductor field-effect transistors).
- Abrasive materials such as grinding wheels, sandpapers, cutting tools, and bulletproof vests.
- Electric vehicles (EVs) and hybrid vehicles for power conversion, improving energy efficiency and reducing heat generation.
- Solar power inverters, LEDs and Aerospace components.